

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **TPV595A** is Designed for Class AB Push Pull, Common Emitter from 470 to 860 MHz Applications.

**FEATURES:**

- Gold Metalization
- Emitter Ballast Resistors
- Internal Input Matching

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	2 x 2.6 A
<b>V<sub>CB</sub></b>	45 V
<b>P<sub>DISS</sub></b>	65 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-50 °C to +200 °C
<b>T<sub>STG</sub></b>	-50 °C to +200 °C
<b>q<sub>JC</sub></b>	2.5 °C/W

**PACKAGE STYLE .250 BAL FLG**

Collector - 2 places  
Emitter connected to flange  
Base - 2 places

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.060 / 1.52	
B	.055 / 1.40	.065 / 1.65
C		.125 / 3.18
D	.243 / 6.17	.255 / 6.48
E	.630 / 16.00	.670 / 17.01
F		.092 / 2.34
G	.555 / 14.10	.565 / 14.35
H	.739 / 18.77	.750 / 19.05
I	.315 / 8.00	.327 / 8.31
J	.002 / 0.05	.006 / 0.15
K	.055 / 1.40	.065 / 1.65
L	.075 / 1.91	.095 / 2.41
M		.190 / 4.83
N	.245 / 6.22	.257 / 6.53

Order Code: **ASI10835**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 40 mA	25	28		<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 20 mA    R <sub>BE</sub> = 51 Ω	40			<b>V</b>
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 20 mA	45			<b>V</b>
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 20 V			5.0	<b>mA</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 5 mA	3.0			<b>V</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 20 V    I <sub>C</sub> = 500 mA	10			<b>--</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 25 V			20	<b>pF</b>
<b>P<sub>G</sub></b>	V <sub>CE</sub> = 25 V    I <sub>C</sub> = 2 x 900 mA    P <sub>REF</sub> = 14 W	8.5	9.5		<b>dB</b>
<b>IMD<sub>3</sub></b>	F = 860 MHz Vision = -8 dB    Sound = -7 dB    SB = -16 dB			-47	<b>dB</b>